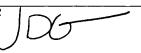
32	L Number	Hits	Search Text	DB	Time stamp
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	b	0	"inquid crystai" adj "sealant material"		2002/10/02 16:30
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8 3 "liquid crystal" near "sealant material"  - 2 "6330099"  - 2 "6330099"  - 2 "6362861"  - 2 "6362861"  - 2 "6362861"  - 2 "3 "Agilent Technologies".AS. and 349/190  - 2 "Agilent Technologies".AS. and 349/190  - 0 "Agilent Technologies".AS. and 349/190  - 0 "Anistropic etch" adj "filling hole"  - 0 "anistropic etch" adj "liquid crystal filling hole"  - 0 "anistropic etch" adj "liquid crystal filling hole"  - 0 "anistropic etch" adj "liquid crystal filling hole"  - 1 1 "anisetropic etch" adj "liquid crystal"  - 1 1 "anisetropic etch" adj "silicon wafer"  - 1 2 "6320010/02 16:31  - 2002/10/02 16:31  - 2002/10/02 10:29  - 2002/10/02 10:36  - 2002/10/02 10:36  - 2002/10/02 10:36  - 2002/10/02 10:36  - 2002/10/02 10:36  - 3 3 "liquid crystal"  - 3 3 3 "liquid crystal"  - 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4	7	0	"liquid crystal" adi "sealant material"		2002/10/02 16:31
SEO, JPG; DERMENT; IEM TOB   USPAT; US-PGUB; EFO, JPG; DERM					
8 3 "liquid crystal" near "sealant material" USPAT; USPOFUB; EPG; JPG; DGEMENT; IBM TDB USPAT;				EPO; JPO;	
3				DERWENT;	
-		_			
- 2 "6330099"	8	3	"liquid crystal" near "sealant material"		2002/10/02 16:31
- 2 "6330099"				1	-
- 2 "6330099"  - 2 "6362861"  - 2 "6362861"  - 2 "6362861"  - 2 231 "Agilent Technologies".AS.  - 0 "Agilent Technologies".AS.  - 0 "Agilent Technologies".AS. and 349/190  - 0 "Agilent Technologies".AS. and 349/190  - 0 "Agilent Technologies".AS. and 349/190  - 0 "anistropic etch" adj "filling hole"  - 0 "anistropic etch" adj "liquid crystal filling hole"  - 0 "anistropic etch" adj "liquid crystal filling hole"  - 0 "anistropic etch" adj "liquid crystal"  - 1 1 "anisotropic etch" adj "silicon wafer"  - 2002/10/02 10:29  2002/10/02 10:29  2002/10/02 10:29  2002/10/02 10:37  2002/10/02 10:37  2002/10/02 10:47  2002/10/02 10:47  2002/10/02 10:48					
- 2 "6330099" USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; USPĀT USPĀT USPĀT USPĀT USPĀT USPĀT USPĀT USP					
- 2231 "Agilent Technologies".AS.	_	2	"6330099"		2002/10/02 16.28
EPO; JPO; DERWENT; LIM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; LIM TDB US-PAT; US-PGPUB; EPO; JPO; DERWENT; LIM TDB USPAT; USPAT		_			2002,10,02 10.20
DERWENT; INM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-P				1	
Tem TDB					
- 2231 "Agilent Technologies".AS. US-PGPUB; EPPO, JPO; DERMENT; IBM_TDB USFAT; US-PGPUB; EPO, JPO; DERMENT; IB				IBM_TDB	-
- 2231 "Agilent Technologies".AS.  - 2231 "Agilent Technologies".AS.  - 0 "Agilent Technologies".AS. and 349/190 USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM T	-	2	"6362861"		2002/10/02 10:29
DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT				· ·	
- 2231 "Agilent Technologies".AS.					
- 2231 "Agilent Technologies".AS. USPĀT; US-PGPUB; EPC; JPC; DERWENT; IBM TDB US-PGPUB; EPC;					
- 0 "Agilent Technologies".AS. and 349/190 US-PGPUB; EPO; JPO; DERWENT; IBM TDB USFAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO	_	2221	"Agilent Technologies" AS		2002/10/02 10:36
- 0 "Agilent Technologies".AS. and 349/190 USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DE	_	2231	Agilent recumologies".A5.		2002/10/02 10:36
- 0 "Agilent Technologies".AS. and 349/190 USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; USPĀT USPĀ					
- 0 "Agilent Technologies".AS. and 349/190 USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; JPO; DERWE					
- 0 "Agilent Technologies".AS. and 349/190 USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; JPO; DERWENT; EPO;		,			
US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; USPĀT;	-	0	"Agilent Technologies".AS. and 349/190		2002/10/02 10:37
DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; TBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; TBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;					
- 0 "anistropic etch" adj "filling hole"  - 0 "anistropic etch" adj "liquid crystal USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO;					
- 0 "anistropic etch" adj "filling hole"  - 0 "anistropic etch" adj "liquid crystal EPG; JPG; DERWENT; IBM TDB USFĀT; US-PGPUB; EPG; JPG; DERWENT; US-PGPUB; EPG; DERWENT; US-PG					
US-PGPUB; EPO; JPO; DERWENT; IBM TDB US-PGPUB; Filling hole"  0 "anistropic etch" adj "liquid crystal US-PGPUB; EPO; JPO; DERWENT; IBM TDB US-PGPUB; EPO; JPO; DERWENT;			Hanistronia otohu add ufillian halau		2002/10/02 10:46
Comparison of the property o	_	U	anistropic etch" adj "filfing noie"		2002/10/02 10:46
DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;					
- 0 "anistropic etch" adj "liquid crystal USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; ISPO; JPO; DERWENT; JP					
O "anistropic etch" adj "liquid crystal USPĀT; US-EGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DER				1	
filling hole"  "anistropic etch" adj "liquid crystal"  "anistropic etch" adj "liquid c	_	0	"anistropic etch" adj "liquid crystal	_	2002/10/02 10:47
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;			filling hole"	US-PGPUB;	
- 0 "anistropic etch" adj "liquid crystal"  - 153 (349/190).CCLS.  - 440 (438/30).CCLS.  1 "anisotropic etch" adj "silicon wafer"  1 "anisotropic etch" adj "silicon wafer"    IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; ISM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;					
- 1 "anisotropic etch" adj "liquid crystal" USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT;				· ·	
US-PGPUB; EPO; JPO; DERWENT; IBM TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT;		_	Handahanada ahakii - 34   022 12   12   12   12   12   12   12		2002/10/02 12 42
EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	- 1	0	"anistropic etch" adj "liquid crystal"		2002/10/02 10:48
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
IBM_TDB   USPAT; US-PGPUB; EPO; JPO; DERWENT;					
- 153 (349/190).CCLS. USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					.
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	_	153	(349/190).CCLS.		2002/10/02 15:20
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
- 440 (438/30).CCLS. USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	1				
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; DERWENT; DERWENT; DERWENT; DERWENT;	-	440	(438/30).CCLS.		2002/10/02 12:46
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;					
- 1 "anisotropic etch" adj "silicon wafer"   IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;   DERWENT;					
- 1 "anisotropic etch" adj "silicon wafer" USPĀT; US-PGPUB; EPO; JPO; DERWENT;					
US-PGPUB; EPO; JPO; DERWENT;	_	1	"anisotropic etch" adi "silicon wafer"		2002/10/02 12:55
EPO; JPO; DERWENT;		1	aniibotiopic ccen adj bilicon water		
DERWENT;					
TRM TOB				· ·	
				IBM TDB	

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-	3	"anisotropic etch" near "silicon wafer"	USPAT; US-PGPUB; EPO; JPO;	2002/10/02 12:56
_	61	"anisotropic etching" adj "silicon wafer"	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/10/02 13:14
-	0	"anisotropic etching" near "liquid crystal"	DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/10/02 13:15
-	0	"anisotropic etching" near "liquid crystal substrate"	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/10/02 13:15
_	708	"anisotropic etching" near "substrate"	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/10/02 13:23
_	144	(349/154).CCLS.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/10/02 13:26
_	10	"injection hole" adj "substrate"	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/10/02 13:43
-	0	"sealant" adj "glue, epoxy, solder"	EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/10/02 13:46
_	0	"sealant material" adj "glue, epoxy,and	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/10/02 13:46
_	311	solder"	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13.54
	311	"sealant" adj "epoxy"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/02 13:54
-	3	"liquid crystal" adj "microdisplays"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/10/02 14:22
-	83	"testing" adj "liquid crystal display"	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/02 14:29
-	0	"testing" adj "liquid crystal micro display"	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/02 14:27
-	0	"testing" adj "sealing hole"	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/02 14:29
			IBM_TDB	



_	0	"testing" adj " liquid crystal sealing	USPAT;	2002/10/02 14:30
		hole"	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	2	"6330099"	USPAT;	2002/10/02 15:09
	_		US-PGPUB;	2002/10/02 13:09
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	(349/190 and testing).CCLS.	USPĀT;	2002/10/02 15:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		240/100 11 1 11	IBM_TDB	
-	0	349/190 adj testing	USPAT;	2002/10/02 15:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	0	349/190 near testing	IBM_TDB USPAT:	2002/10/02 15:18
		3137130 near resering	US-PGPUB;	2002/10/02 13:18
İ			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	"349/190" near "testing"	USPAT;	2002/10/02 15:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		H240/100B - 1' Br - 1' B	IBM_TDB	
-	0	"349/190" adj "testing"	USPAT;	2002/10/02 15:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	475	(438/15).CCLS.	USPAT;	2002/10/02 15:21
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	2002/10/02 13.21
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	98	(injection hole) adj (glue)	USPĀT;	2002/10/02 16:19
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	L		IBM_TDB	

438/15 -> Lay to successful search
because Applicant's methods
are drawn Crom
Semiconductor technology
(testing, Jailure analysis)

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